N-Channel and P-Channel Complementary MOSFET

Product Summary

NMOS

V_{DS}	30V
I_D	40A
$R_{DS(ON)}$(at V_{GS}=10V)	8.5m
$R_{DS(ON)}$(at V_{GS}=4.5V)	14m

PMOS

V_{DS}	-30V
I_D	-40A
$R_{DS(ON)}$(at V_{GS}=-10V)	12m
$R_{DS(ON)}$(at V_{GS}=-4.5V)	20m

100% EAS Tested
100% V_{DS} Tested

General Description

A R PU= R 9C: 32A aRPU YT
2 PRYR a NPXNTRS URNaQV VNaV
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

9 NQ YaPUVT
5N Q YaPURQN d high frequency circuits
B VaR aQVR R Y

Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	NMOS	PMOS	Unit
Drain-source Voltage		V_{DS}	30	-30	V
Gate-source Voltage		V_{GS}	±20	±25	V
Drain Current	T_A=25℃	I_D	11	-11	A
	T_A=100℃		7	-7	
	T_C=25℃		40	-40	
	T_C =100℃		25	-25	
Pulsed Drain Current [A]		I_{DM}	140	-160	A
Avalanche energy [B]		EAS	56	90	mJ
Total Power Dissipation [C]	T_A=25℃	P_D	2.5	2.5	W
	T_A=100℃		1	1	
	T_C=25℃		50	54	
	T_C =100℃		20	21	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55 +150	-55 +150	℃

Thermal resistance

Parameter		Symbol	NMOS		PMOS		Units
			Typ	Max	Typ	Max	
Thermal Resistance Junction-to-Ambient [D]	Steady-State	R 7.	40	50	40	50	/W

Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG40NP03B	F1	YJG40NP03B	5000	10000	100000	13 reel

NMOS Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250 .	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	.
		V_{DS}=30V, V_{GS}=0V, Tj=150	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= 20V, V_{DS}=0V	-	-	100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250 .	1.0	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	6.5	8.5	m
		V_{GS}=4.5V, I_D=10A	-	10	14	
Diode Forward Voltage	V_{SD}	I_S=20A, V_{GS}=0V	-	0.9	1.2	V
Gate resistance	R_G	f=1MHz, Open drain	-	2.5	-	
Maximum Body-Diode Continuous Current	I_S		-	-	40	A
Dynamic Parameters						
Input Capacitance	C_{iss}		-	1050	-	
Output Capacitance	C_{oss}	V_{DS}=15V, V_{GS}=0V, f=1MHz	-			pF

PMOS Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=- .	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V, V_{GS}=0V	-	-	-1	.
		V_{DS}=-30V, V_{GS}=0V, Tj=150℃	-	-	-100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±25V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=- .	-1.2	-1.8	-2.7	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-20A	-	9	12	m
		V_{GS}=-4.5V, I_D=-10A	-	15	20	
Diode Forward Voltage	V_{SD}	I_S=-20A, V_{GS}=0V	-	-0.9	-1.2	V
Gate resistance	R_G	f=1MHz	-	17	-	
Maximum Body-Diode Continuous Current	I_S		-	-	-40	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=-15V, V_{GS}=0V, f=1MHz	-	1860	-	pF
Output Capacitance	C_{oss}		-	310	-	
Reverse Transfer Capacitance	C_{rss}		-	280	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=-10V, V_{DS}=-15V, I_D=-20A	-	38	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	
Gate-Drain Charge	Q_{gd}		-	10	-	
Reverse Recovery Charge	Q_{rr}	I_F=-20A, di/dt=100A/us	-	22	-	nC
Reverse Recovery Time	t_{rr}		-	43	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=-10V, V_{DD}=-15V, ID=-20A R_{GEN}=2.2	-	8	-	ns
Turn-on Rise Time	t_r		-	6	-	
Turn-off Delay Time	$t_{D(off)}$		-	108	-	
Turn-off fall Time	t_f		-	69	-	

A. Repetitive rating; pulse width limited by max. junction temperature.
B. NMOS: T_J=25℃, V_{DD}=25V, V_G=10V, R_G 9 Z 5 6 15A.
PMOS: T_J=25℃, V_{DD}=-25V, V_G=-10V, R_G 9 0.5mH, IAS=-19A.
C. P_d is based on max. junction temperature, using junction-case thermal resistance.
D. The value of R 7. is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in the still air environment with T_A =25℃. The maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

NMOS Typical Electrical and Thermal Characteristics Diagrams

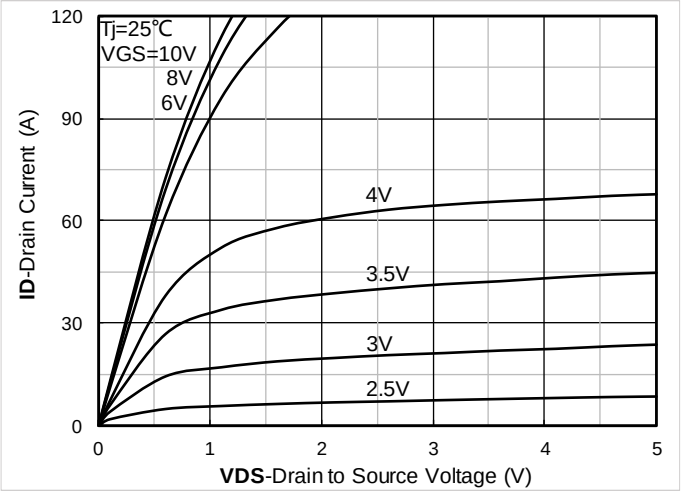

Figure 1. Output Characteristics

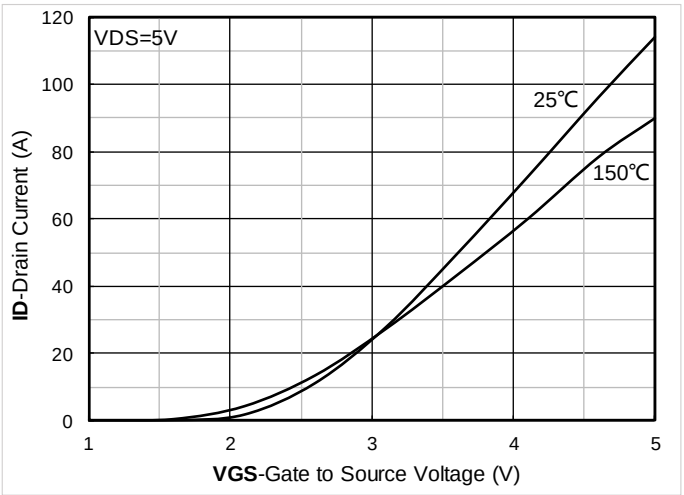

Figure 2. Transfer Characteristics

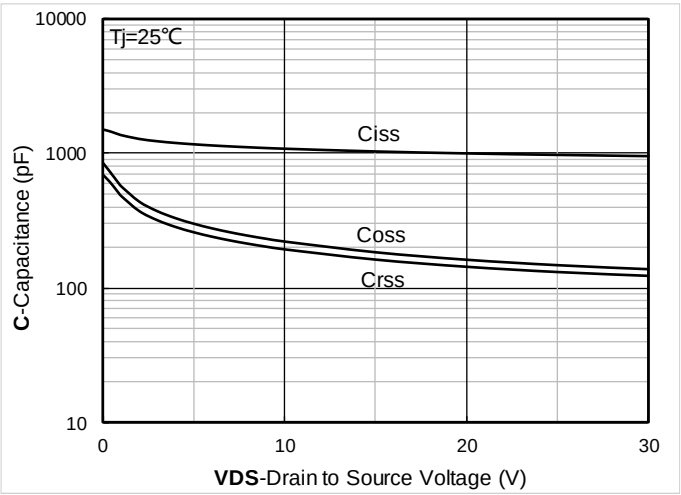

Figure 3. Capacitance Characteristics

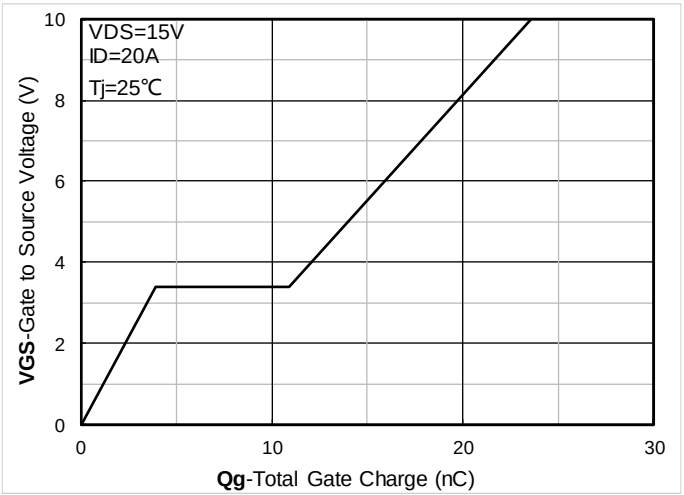

Figure 4. Gate Charge

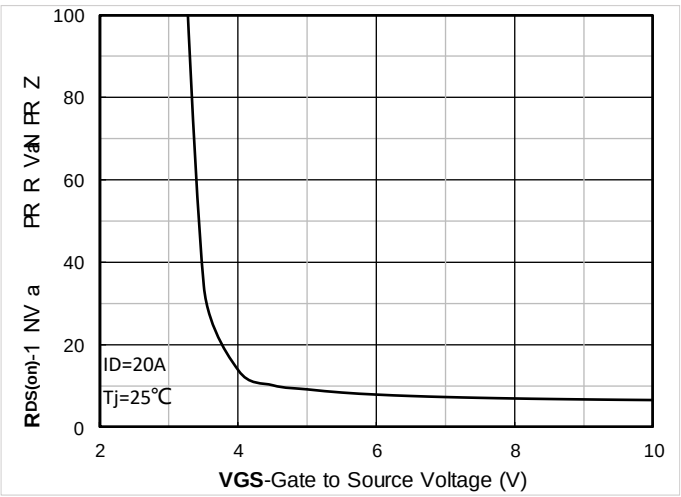

Figure 5. On-Resistance vs Gate to Source Voltage

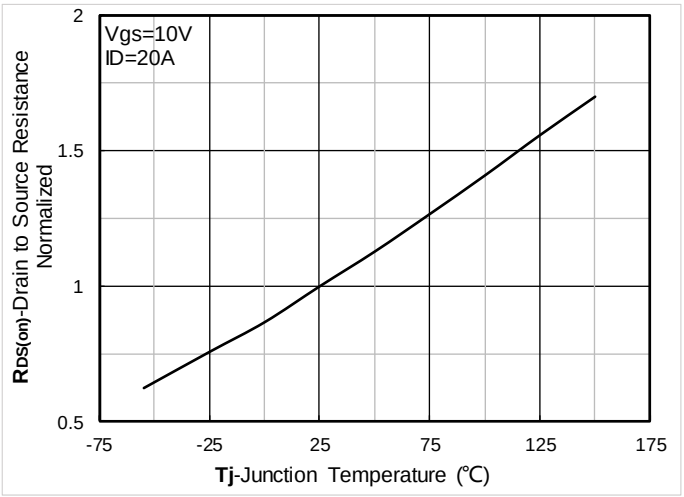

Figure 6. Normalized On-Resistance

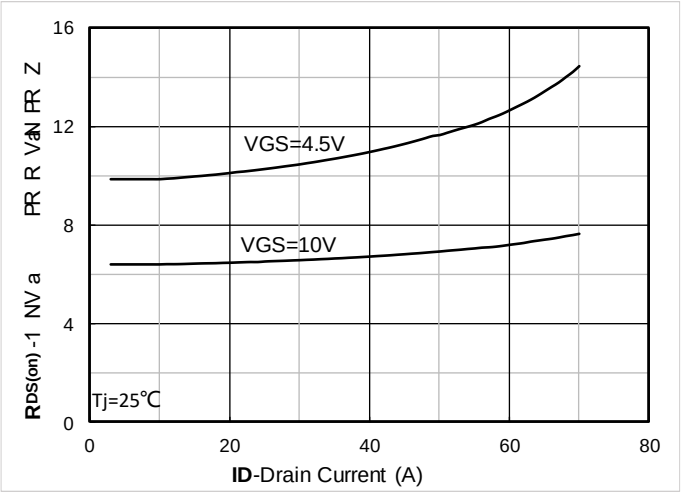

Figure 7. $R_{DS(on)}$ VS Drain Current

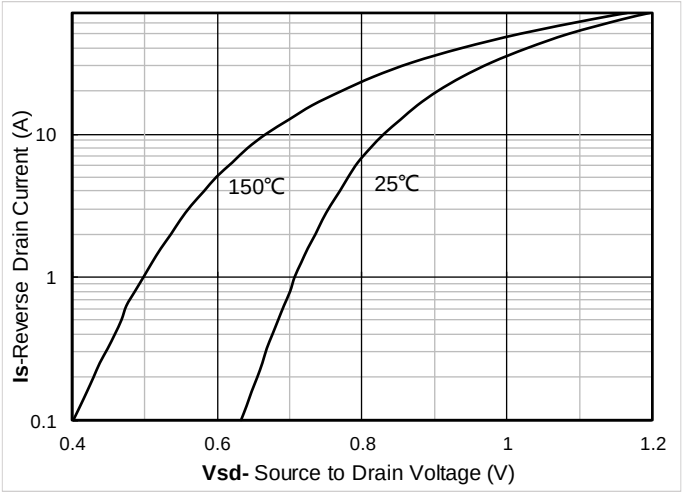

Figure 8. Forward characteristics of reverse diode

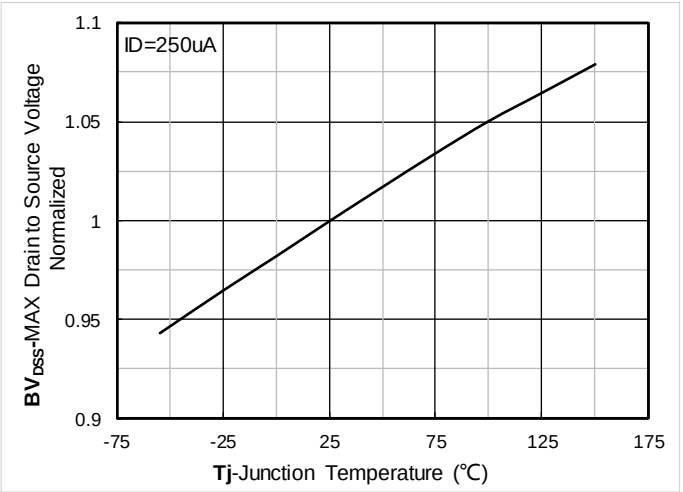

Figure 9. Normalized breakdown voltage

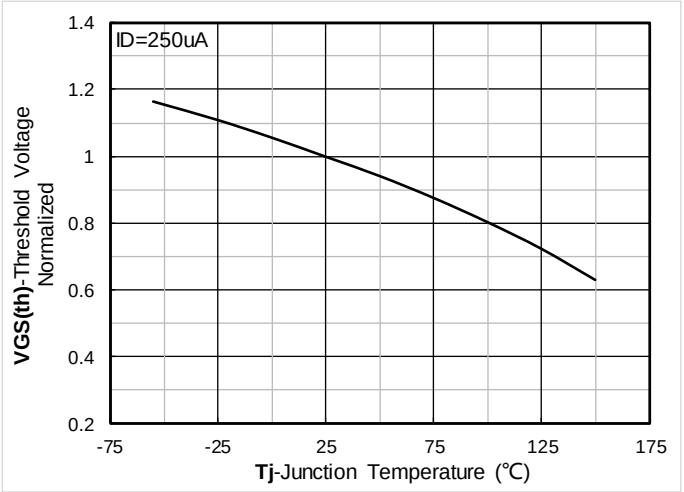

Figure 10. Normalized Threshold voltage

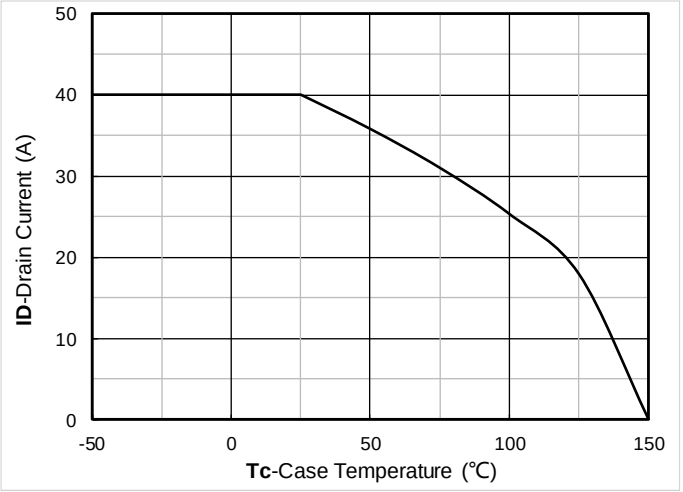

Figure 11. Current dissipation

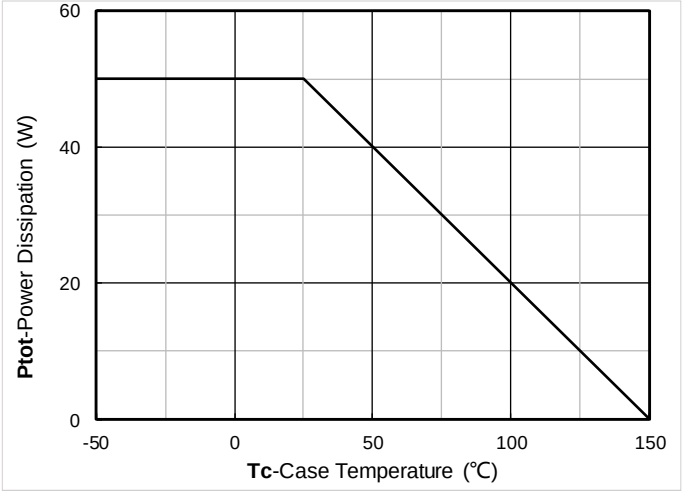

Figure 12. Power dissipation

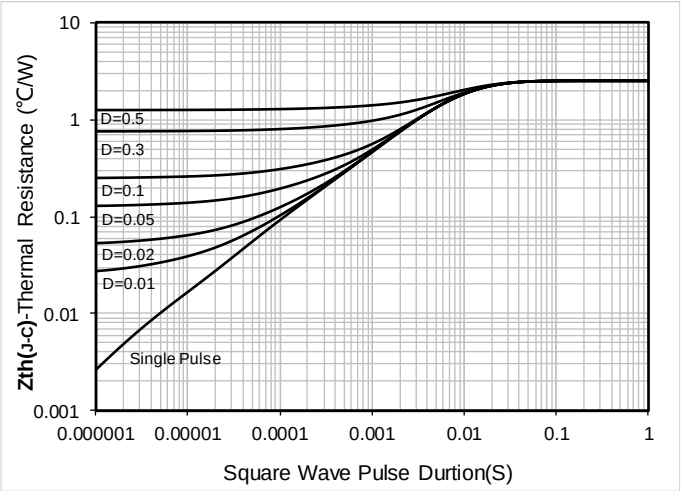

Figure 13. Maximum Transient Thermal Impedance

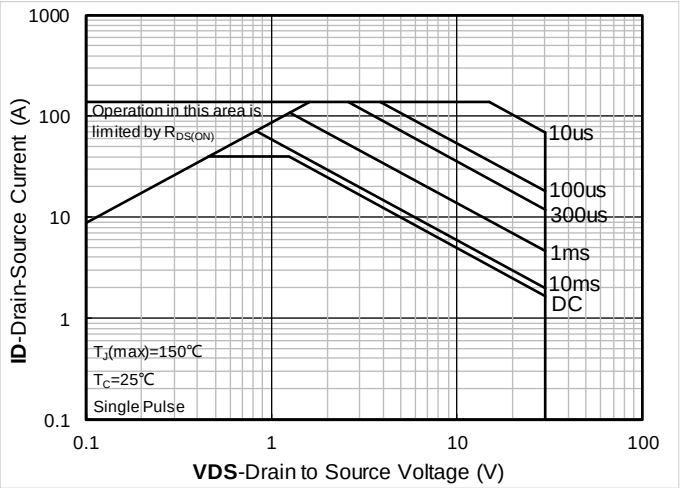

Figure 14. Safe Operation Area

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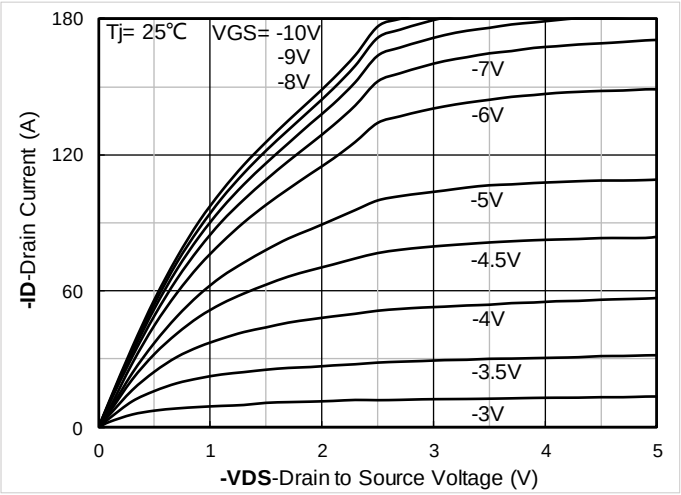
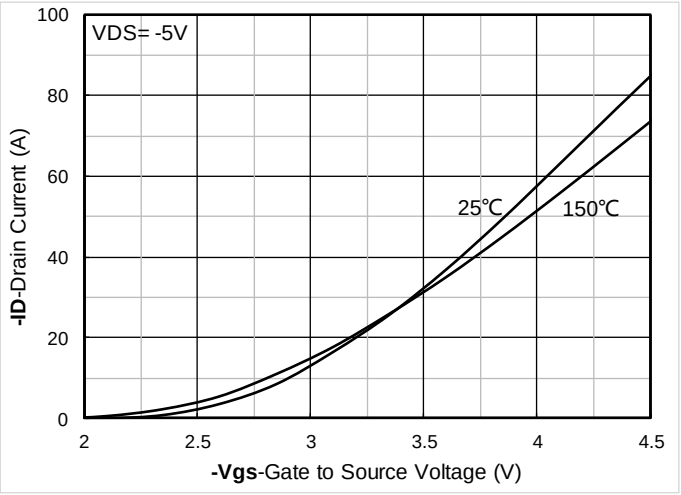


Figure 1. Output Characteristics



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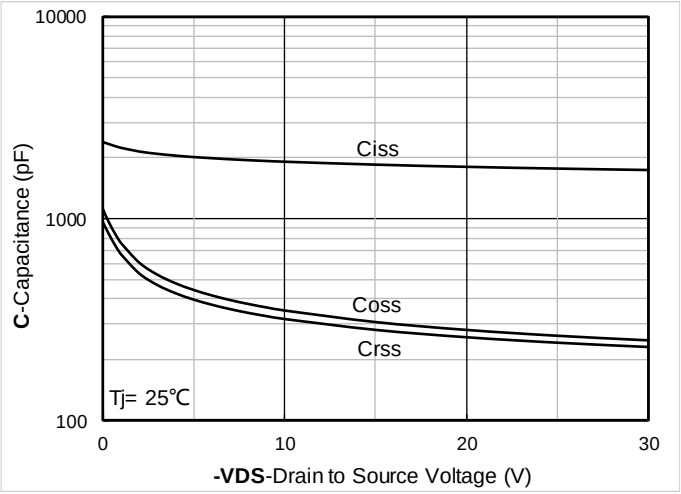

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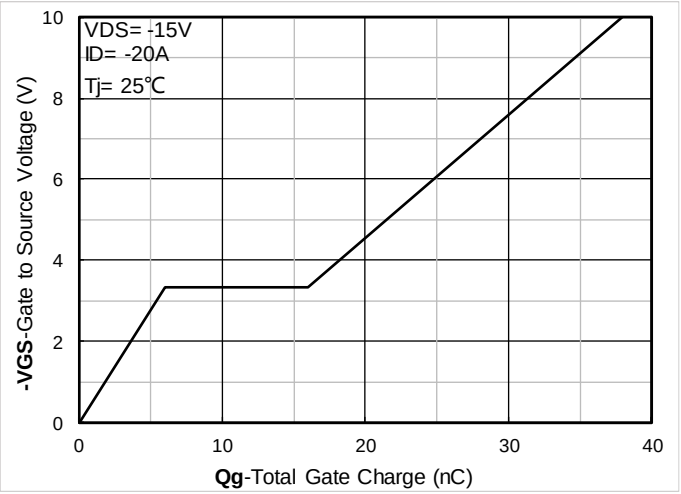
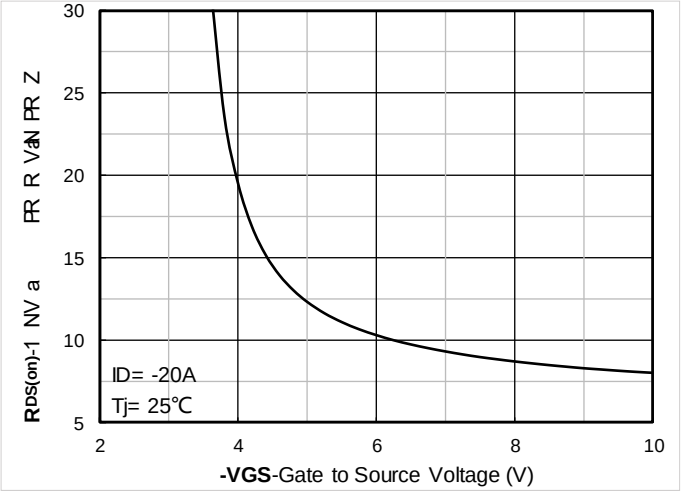


Figure 4. Gate Charge



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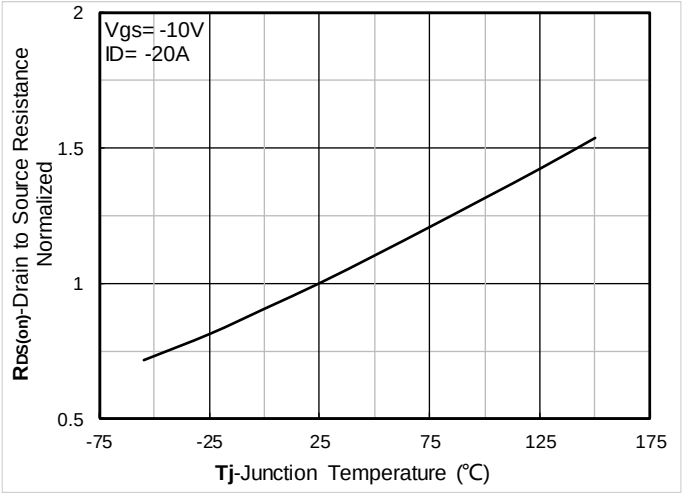
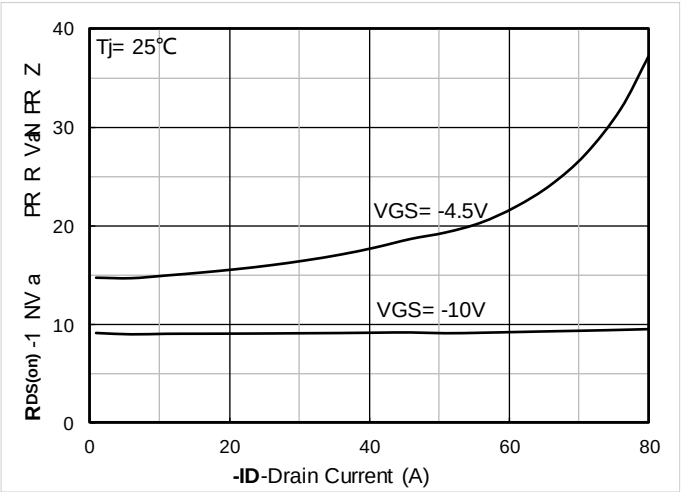


Figure 6. Normalized On-Resistance



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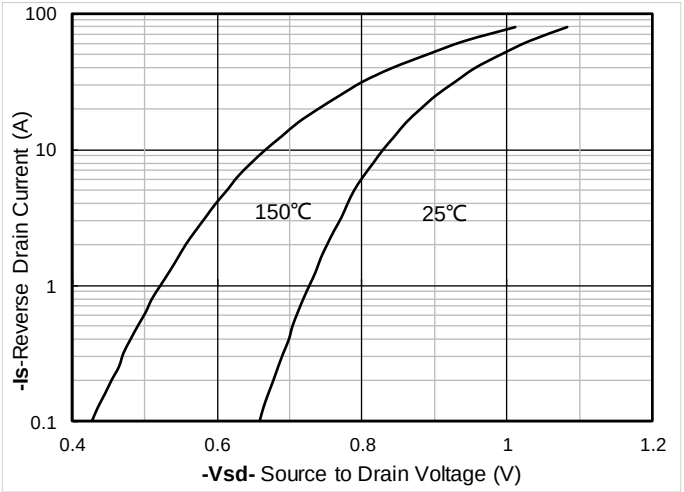

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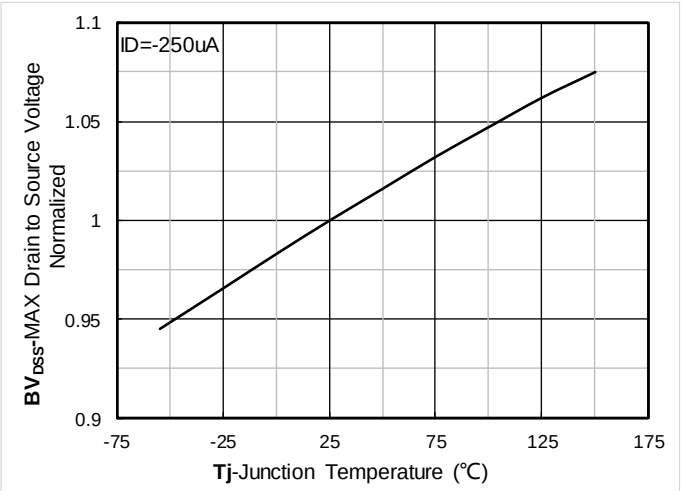


Figure 9. Normalized breakdown voltage

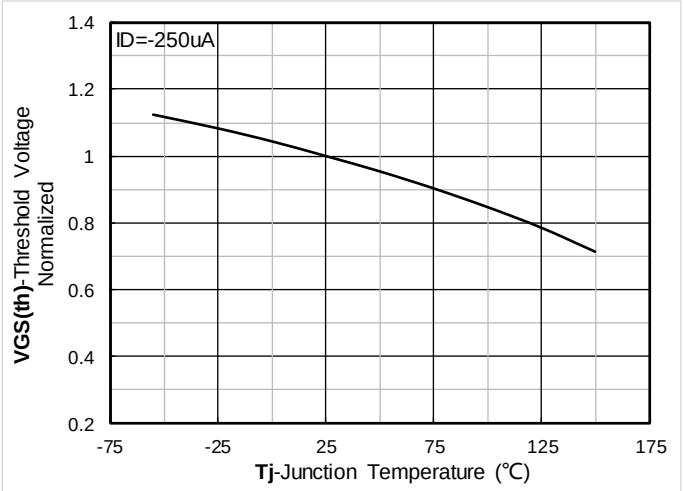


Figure 10. Normalized Threshold voltage

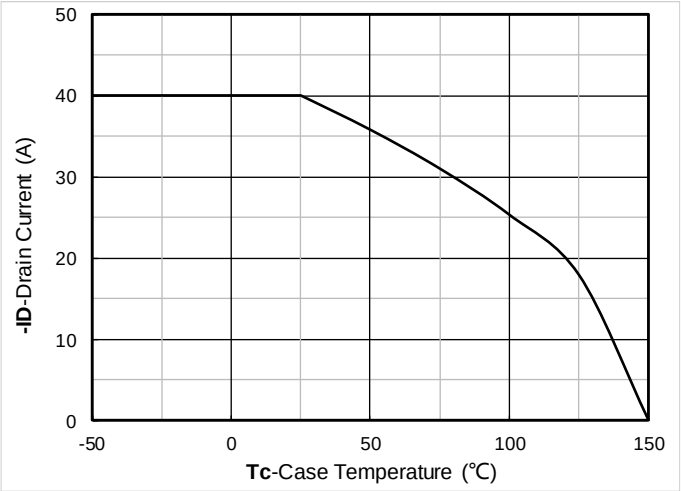


Figure 11. Current dissipation

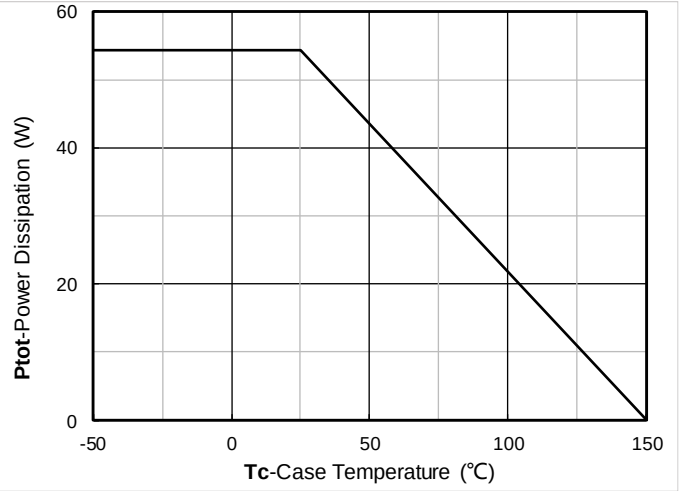
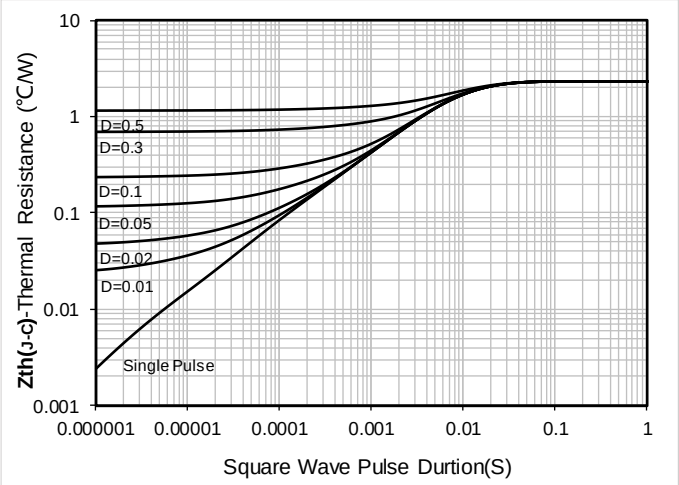


Figure 12. Power dissipation



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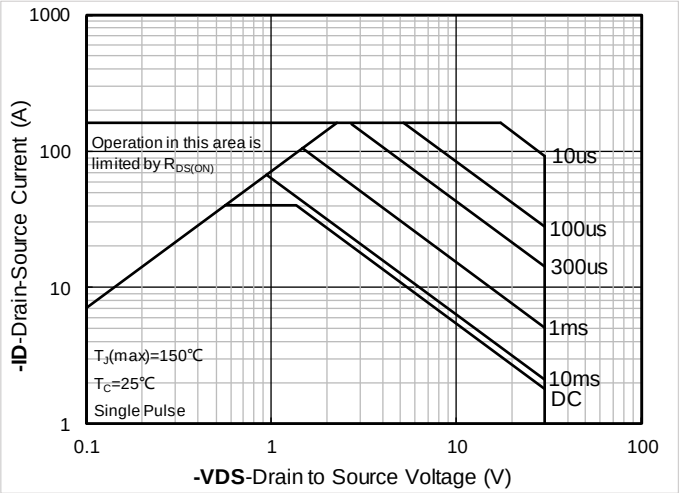
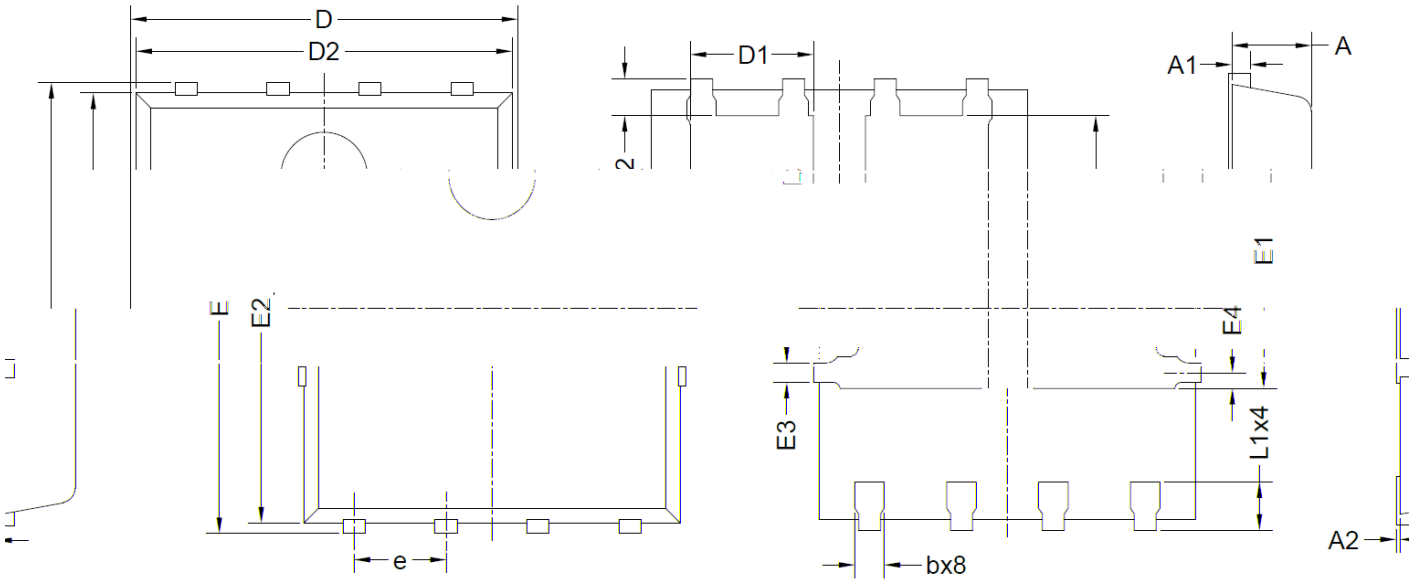


Figure 14. Safe Operation Area

PDFN5060-8L-E-1.1mm Package information

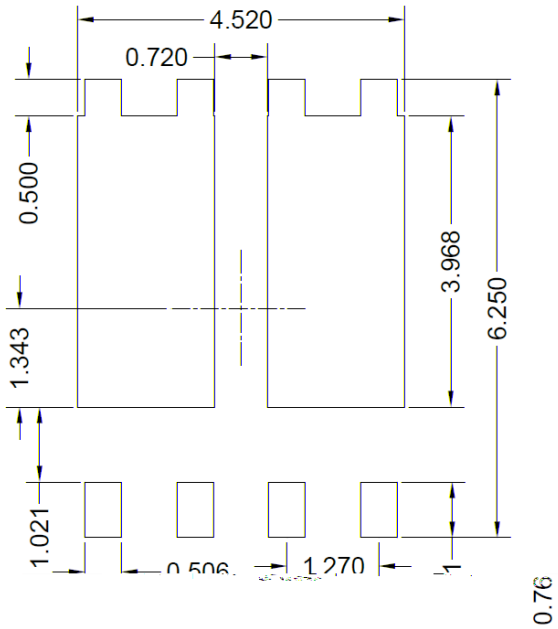


e View
面视图

Top View
正面视图

Bottom View
背面视图

Sid
侧面



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	M
D	5.15	5.35	5
E	5.95	6.15	6
A	1.00	1.10	1
A1		0.254 BSC	
A2			0
D1	1.50	1.70	1
E1	3.52	3.72	3
D2	5.00	5.20	5
E2	5.66	5.86	6
E3		0.254REF	
E4		0.21REF	
L1	0.56	0.66	0
L2		0.50 BSC	
b	0.31	0.41	0
e		1.27 BSC	

meters.

ce purposes only.

Note:
1.Controlling dimension:in milli
2.General tolerance:±0.10mm.
3.The pad layout is for referen

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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